

MP86961

20A, 27V Intelli-Phase[™] Solution (Integrated HS/LS FETs and Driver) in a 5x5mm QFN

The Future of Analog IC Technology

DESCRIPTION

The MP86961 is a monolithic Half Bridge with built-in internal power MOSFETs and gate driver. It achieves 20A continuous output current over a wide input supply range.

Integrating the Driver and MOSFETs results in high efficiency due to optimal dead time control and parasitic inductance reduction.

The MP86961 is a Monolithic IC designed to drive up to 20A per phase. Housed in a very small 5x5mm QFN Packge, this device can be operated from 100kHz to 1MHz.

The IC is intended to work with 5V tri-state output controllers.

The MP86961 is ideal for notebook applications where efficiency and small size are a premium.

FEATURES

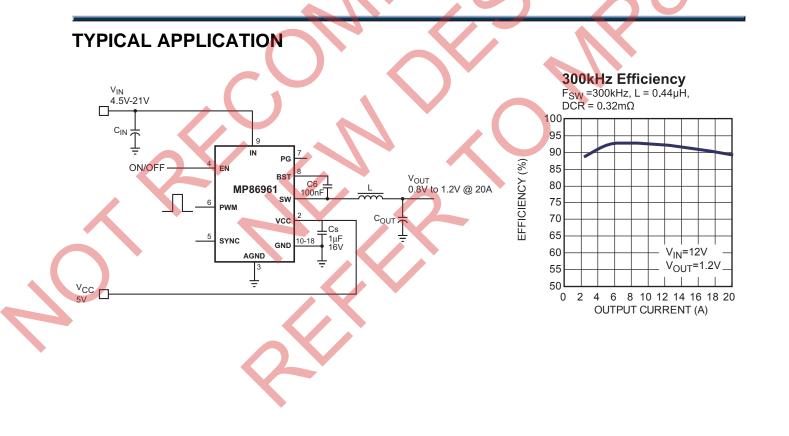
- Wide 4.5V to 21V Operating Input Range
- 20A Output Current
- Simple Logic Interface(5.0V)
- Operate from 100kHz to 1MHz
- Accepts 3-state PWM Input
- Suitable for single-/multi-phase operation
- Available in a 5mm x 5mm QFN Package
- ROHS6 Compliant

APPLICATIONS

- Power modules
- Notebook, Core Voltage
- Graphic Card Core Regulators

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This Product is Patent Pending





ORDERING INFORMATION

Part Number*	Package	Top Marking	Free Air Temperature(T _A)
MP86961DU	5x5 QFN	86961DU	-40°C to +85°C
For F	* For Tape & Reel, add su RoHS compliant packaging, ad		
	PACKAGE	REFERENCE	
	PIN 1 ID		
	······ ····	sw (17) GND	
	AGND (3) IN EN (4)	GND (16 GND (15 GND	
	SYNC	SW	
	PWM 6. IN PG 7.	GND (18) GND SW (12) GND	
	BST (.8.) IN	GND (11 GND	
	IN (9)	sw .10 GND	
	CONNECT T		
BSOLUTE MAX	IMUM RATINGS ⁽¹⁾	Thermal Resist	
apply Voltage V _{IN}		5x5 QFN	
W		Notes:	
	to V _{IN} + 0.3V (+3V	The maximum allow	i <mark>ngs may da</mark> mage the device. vable power dissipation is a function of the
ST	V _{SW} + 6V 0.3V to +6V		temperature $T_J(MAX)$, the junction-to- sistance θ_{JA} , and the ambient temperature
Other Pins	0.3V to +6V	T _A . The maximum	allowable continuous power dissipation at
	sipation $(T_A = +25^{\circ}C)^{(2)}$	$T_A)/\theta_{JA}$. Exceeding	ature is calculated by P _D (MAX)=(T _J (MAX)- the maximum allowable power dissipation
	3.5W	will cause excessive 3) The device is not	e die temperature. guaranteed to function outside of its
	150°C	operating conditions	- -
		4) Measured on appro	ximately 4" square of 4-layer PCB.
	65°C to +150°C		
	rating Conditions ⁽³⁾		
	4.5V to 5.5V (T _J)40°C to +125°C		
Jerating Junct. Temp	(1 _j)40°C 10 +125°C		



ELECTRICAL CHARACTERISTICS

 $V_{IN} = 12V$, $T_A = +25^{\circ}C$, unless otherwise noted.

Parameters	Symbol	Condition	Min	Тур	Max	Units
I _{cc} Standby	I _{CC Stdby}	V _{CC} =5V, PWM=EN=LO		230	300	μA
I _{IN} (Shutdown)	I _{IN (Off)}	$V_{\rm CC} = 0V$		1	5	μA
I _{IN} Standby	I _{IN_Stdby}	V _{CC} =5V, PWM=EN=LO		1		μA
Rise Time		I _{OUT} = 20A		5		ns
Fall Time		I _{OUT} = 20A		3		ns
Minimum On-Time				55		ns
Dead-Time Rising				5		ns
Dead-Time Falling				10		ns
V _{CC} Under Voltage Lockout Threshold Rising				3.7	4.2	V
V _{CC} Under Voltage Lockout Threshold Hysteresis				470		mV
SYNC Pull-Up Current	I _{SYNC}	SYNC=0V		-14		μA
SYNC Logic High Voltage			2			V
SYNC Logic Low Voltage					0.4	V
EN Input Low Voltage					0.4	V
En Input High Voltage			2		C	V
Power Good Rds(on)		EN=0V		20		Ω
PWM Input						
Input Current	I _{PWM}	V _{PWM} =5V V _{PWM} =0V		90 -90	0	μΑ μΑ
PWM Low to Tri-State Rising Threshold				1.7		V
PWM Tri-State to High Threshold				3.7		V
PWM High to Tri-State Rising Threshold				3.4		V
PWM Tri-State to Low Threshold				1		V
Tri-State Shutdown Holdoff Time	t _{TSSHD}	V _{cc} =5V, Temperature=25°C		80		ns
UG/LG Three-State Propagation Delay				20		ns
USW Turn-Off Propagation Delay		V _{cc} =5V		30		ns
LSW Turn-Off Propagation Delay		V _{cc} =5V		10		ns
USW Turn-On Propagation Delay	t _{PDUH}	V _{cc} =5V		20		ns
LSW Turn-On Propagation Delay		V _{cc} =5V		45		ns



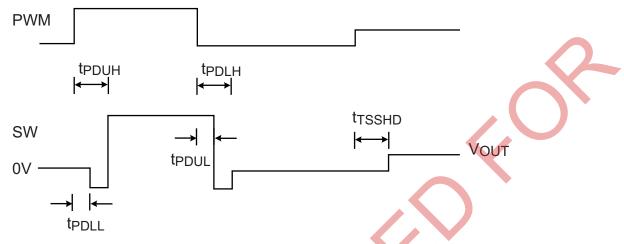
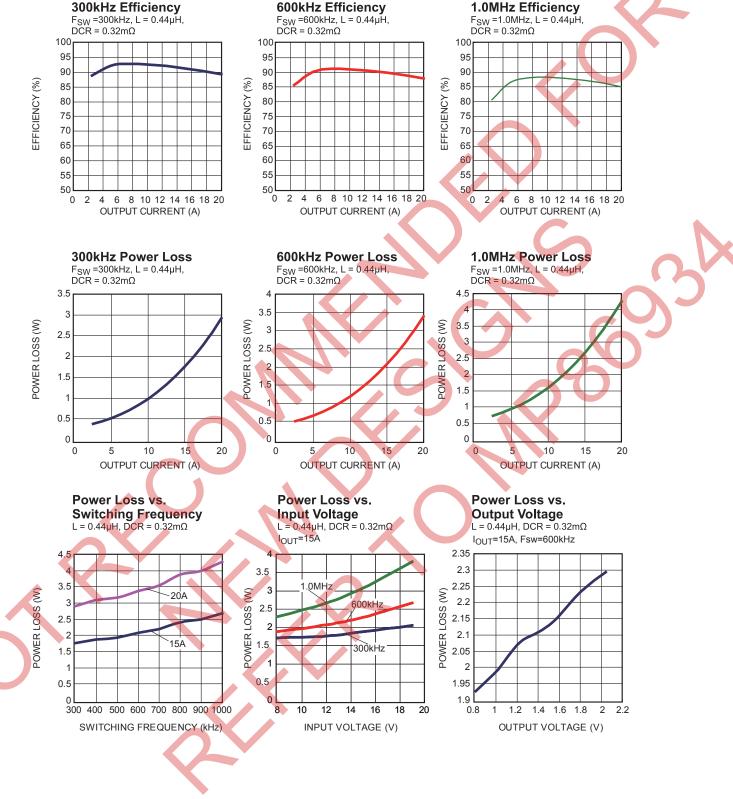
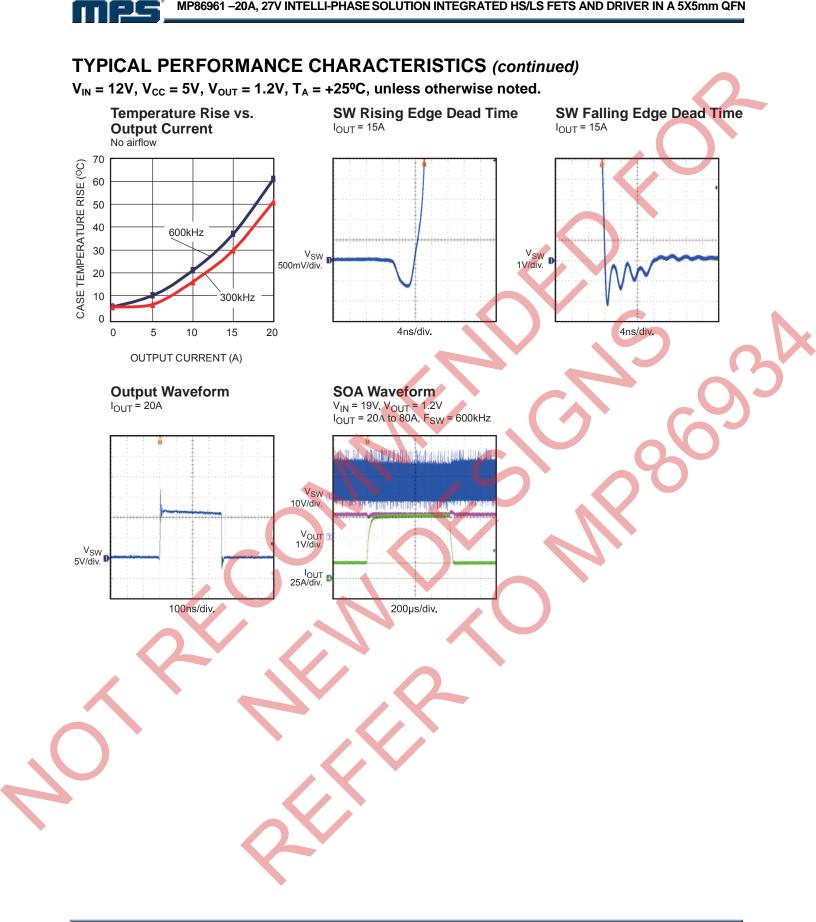


Figure 1- Timing Diagram

PIN FUNCTIONS

Pin #	Name	Description		
1	NC	Not Connected.		
2	VCC	Low-Side Driver Bias Supply. Decouple with a 1µF ceramic capacitor.		
3	AGND	Signal Ground.		
4	EN	Active High On/Off Control. Pulling this Pin Low forces the SW pin to be in a high impedance state.		
5	SYNC	Leaving this pin Open enables the Lower Synchronous Switch. Pulling it Low forces the Lower Switch into Diode Emulation mode.		
6	PWM	Pulse Width Modulation Control. Accepts three state input. Force PWM to midstate or open to place SW into high impedance state.		
7	PG	Power Good. Open drain output is low impedance to ground until internal supplies are good.		
8	BST	Bootstrap. This capacitor is needed to drive the power switch's gate above the supply voltage. It is connected between SW and BST pins to form a floating supply across the power switch driver.		
9 Exposed Pad	IN	Supply Voltage. C_{IN} is needed to prevent large voltage spikes from appearing at the input.		
10–18 Exposed Pad	GND	Power Ground.		
Exposed Pad	SW	Switch Output. These pins are fused together.		



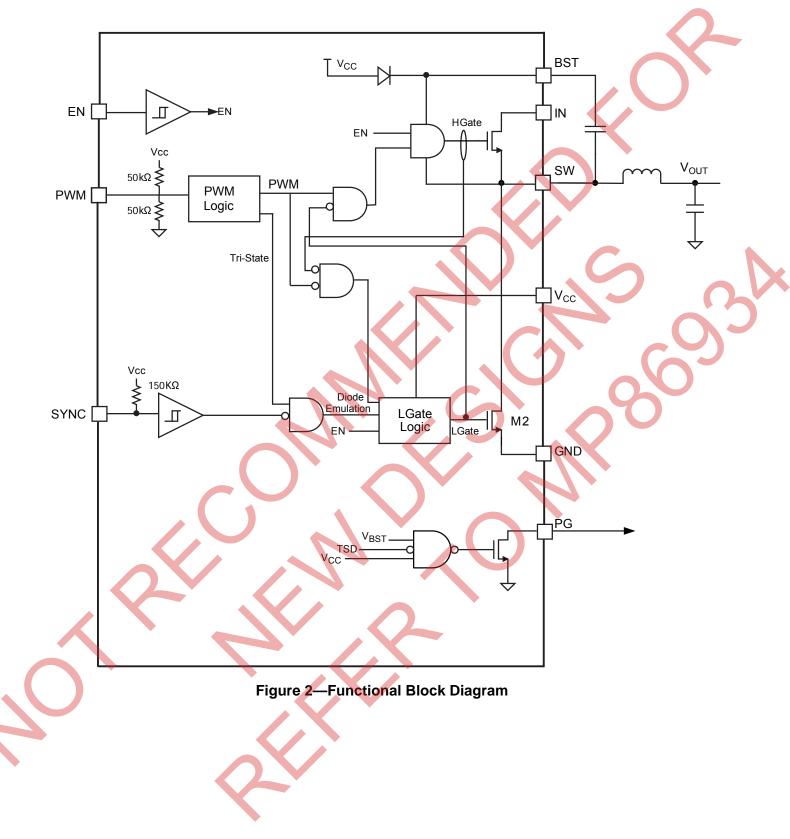




EFFICIENCY MEASUREMENT SETUP lin lout \rightarrow 0.44µH **#330µF**∔ 22µF #220µF+100µF 22uF 0.1µF GND **≷10k** Measured Vout 9 ₈ 0.1µF 10nF IN 4 EN $|\mathsf{EN}\rangle$ BST ⁶PWM SW PWM MP86961 PG 7 Icc 1 N/C 2 5 SYNC VCC 1µF GND 10-18 ³AGND _



BLOCK DIAGRAM





OPERATION

The MP86961 is a 20A Monolithic Half Bridge driver with MOSFETs ideally suited for single-/multi-phase Buck regulators.

Once the EN, V_{IN} , V_{CC} and V_{BST} signals are sufficiently high, operation begins. BST voltage has a typical rising UVLO of 2.2V and a falling UVLO of 2.0V. When BST is below the UVLO voltage, the device will be off.

MP86961 can work with most PWM controllers. The device accepts PWM signal from 100kHz up to 1MHz. There is an internal resistor divider to put PWM voltage to tri-state region if the PWM pin is open.

Internally, SYNC is tied to V_{CC} through a resistor. By default, the device will operate in synchronous mode. To enter Diode Emulation mode, drive SYNC pin LOW.

Startup and Shutdown Sequence

MP86961 can work with any startup or shutdown sequencing combination of V_{IN} , V_{CC} and EN. If PWM signal is present, the MP86961 will start working whenever V_{IN} , V_{CC} and EN are ready. On the other hand, if any of these signals is not ready, the MP86961 will stop working. However, it is recommended to turn on and turn off the device through the EN pin.

PCB Layout Guideline

PCB layout is very important to achieve stable operation. Please follow these guidelines to achieve optimal performance.

1) Keep the path of switching current short and minimize the loop area formed by input capacitor. Keep the connection between SW pin and input power ground as short and wide as possible.

2) Always place some input bypass ceramic capacitors next to the device and on the same layer as the device. Do not put all of the input bypass capacitors on the back side of the device. Use as many vias and input voltage planes as possible to reduce the switching spike. BST capacitor and V_{CC} capacitor should also be as close to the device as possible.

3) The recommended external BST cap is 100nF. Do not use a capacitance value lower than 100nF. Place a 1.0Ω resistor between the BST capacitor and BST pin for optimized performance.

4) Do not place via on the pad or on the pin footprint. Doing so may cause soldering issue during the assembling process. Use Figure 3 as a via placement reference.

5) Connect IN, SW and GND to large copper area and use vias to cool the chip to improve thermal performance and long-term reliability. See Figure 4 as an example.

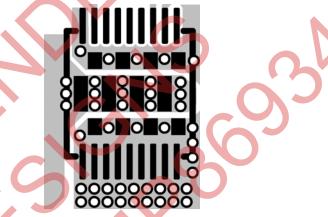


Figure 3—Via Placement Guideline

Do not put via on the device's pad footprint or pin footprint to avoid assembly issue. Use as many vias as possible to cool down the device.

6) Place the V_{CC} decouple capacitor close to the IC. Connect AGND and PGND at the point of V_{CC} capacitor's ground connection.

Recommended SMT Setting

Stencil thickness: 0.12mm

EP Pad Opening: (Stencil opening : Real PCB Size)

Length: 0.85:1 Width: 1:1 Note: The EP pad for Intelli-Phase are IN, SW and GND pad on the bottom.

Solder type: #3



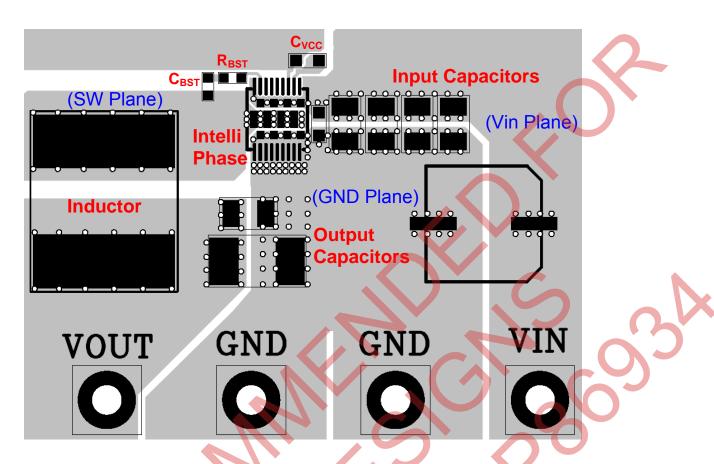
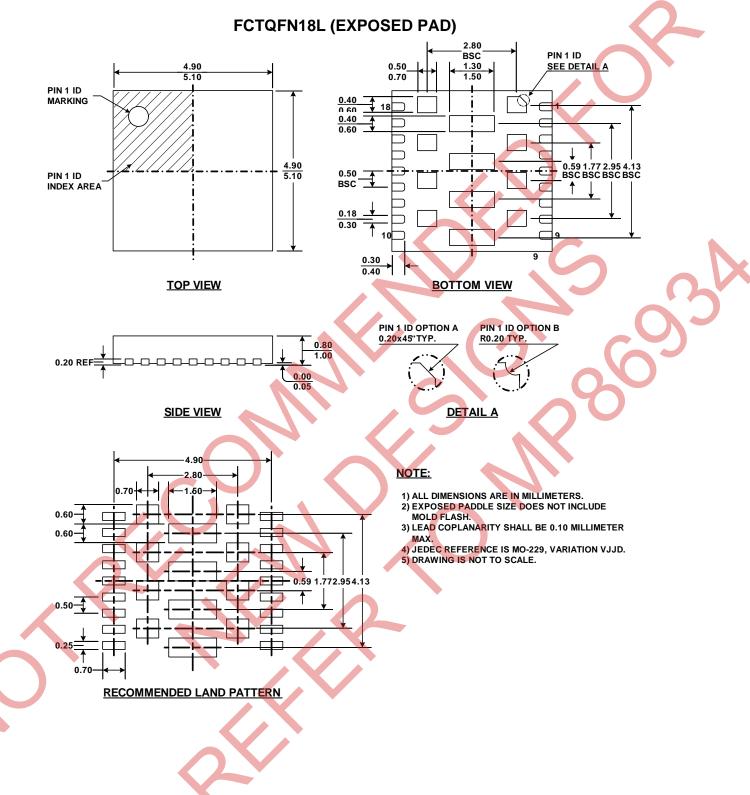


Figure 4—Copper Area Guideline

Use large copper area, many vias and many IN, SW and GND inner layer planes to achieve optimal thermal performance.



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